

1. General description

Dual ultrafast power diode in TO263 (D2PAK) plastic package.

2. Features and benefits

- Low on-state loss
- Ultra low leakage
- Fast switching
- Soft recovery characteristic minimizes power consuming oscillations
- High reverse surge capability
- High thermal cycling performance
- Low thermal resistance

3. Applications

- Home appliance power supply

4. Quick reference data

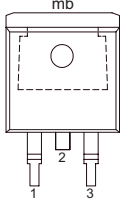
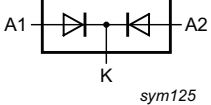
Table 1. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Values | | | Unit |
|-------------------------|-------------------------------------|--|--------|------|------|------|
| Absolute maximum rating | | | | | | |
| V _{RRM} | repetitive peak reverse voltage | | 200 | | | V |
| I _{O(AV)} | average output current | δ = 0.5 ; square-wave pulse; T _{mb} ≤ 143 °C; both diodes conducting; Fig. 1 ; Fig. 2 ; Fig. 3 | 20 | | | A |
| I _{FRM} | repetitive peak forward current | δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 151 °C; square-wave pulse ; per diode | 20 | | | A |
| I _{FSM} | non-repetitive peak forward current | t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse; per diode; Fig. 4 | 125 | | | A |
| | | t _p = 8.3 ms; T _{j(init)} = 25 °C; sine-wave pulse; per diode | 137 | | | A |
| I _{RRM} | repetitive peak reverse current | square-wave pulse; f = 1 kHz; t _p = 2 μs; per diode | 0.2 | | | A |
| V _{ESD} | electrostatic discharge voltage | all pin; human body model; C = 250 pF; R = 1.5 kΩ | 8 | | | kV |
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| Static characteristics | | | | | | |
| V _F | forward voltage | I _F = 20A; T _j = 25 °C; per diode; Fig. 6 | - | 1.06 | 1.15 | V |
| | | I _F = 8 A; T _j = 150 °C; per diode; Fig. 6 | - | 0.76 | 0.85 | V |
| Dynamic characteristics | | | | | | |
| t _{rr} | reverse recovery time | I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _j = 25 °C; per diode; Fig. 7 | - | 18 | 25 | ns |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|------------------------------------|---|---|
| 1 | A | anode |  |  |
| 2 | K | cathode | | |
| 3 | A | anode | | |
| mb | mb | mounting base; connected to cathod | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|--------------|---------|---|---------|
| | Name | Description | Version |
| BYV32EB-200P | TO-263 | plastic single-ended surface-mounted package (DPAK); 3-leads (one lead cropped) | DPAK |

7. Marking

Table 4. Marking codes

| Type number | Marking codes |
|--------------|---------------|
| BYV32EB-200P | BYV32EB-200P |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Values | Unit |
|-------------|-------------------------------------|--|------------|------------------|
| V_{RRM} | repetitive peak reverse voltage | | 200 | V |
| V_{RWM} | crest working reverse voltage | | 200 | V |
| V_R | reverse voltage | DC | 200 | V |
| $I_{O(AV)}$ | average output current | $\delta = 0.5$; square-wave pulse; $T_{mb} \leq 143^\circ\text{C}$; both diodes conducting; Fig. 1 ; Fig. 2 ; Fig. 3 | 20 | A |
| I_{FRM} | repetitive peak forward current | $\delta = 0.5$; $t_p = 25\ \mu\text{s}$; $T_{mb} \leq 151^\circ\text{C}$; square-wave pulse; per diode | 20 | A |
| I_{FSM} | non-repetitive peak forward current | $t_p = 10\ \text{ms}$; $T_{j(\text{init})} = 25^\circ\text{C}$; sine-wave pulse; per diode; Fig. 4 | 125 | A |
| | | $t_p = 8.3\ \text{ms}$; $T_{j(\text{init})} = 25^\circ\text{C}$; sine-wave pulse; per diode | 137 | A |
| I_{RRM} | repetitive peak reverse current | square-wave pulse; $f = 1\ \text{kHz}$; $t_p = 2\ \mu\text{s}$; per diode | 0.2 | A |
| I_{RSM} | non-repetitive peak reverse current | square-wave pulse; $t_p = 100\ \mu\text{s}$; per diode | 0.2 | A |
| T_{stg} | storage temperature | | -65 to 175 | $^\circ\text{C}$ |
| T_j | junction temperature | | 175 | $^\circ\text{C}$ |
| V_{ESD} | electrostatic discharge voltage | all pin; human body model; $C = 250\ \text{pF}$; $R = 1.5\ \text{k}\Omega$ | 8 | 8kV |

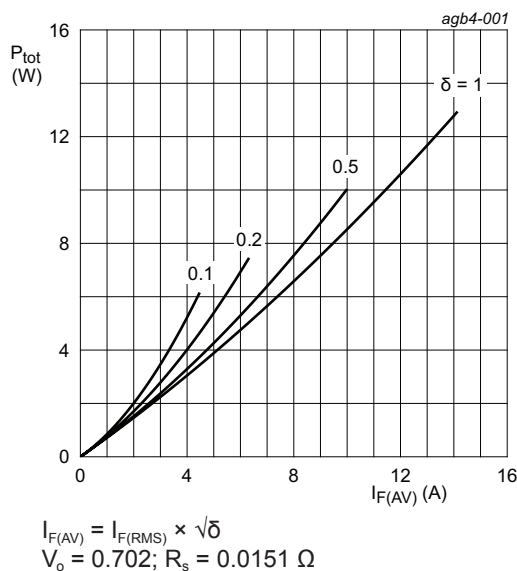


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode

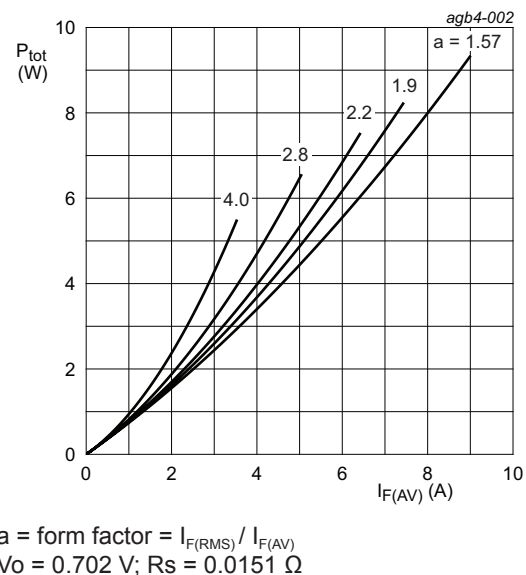


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

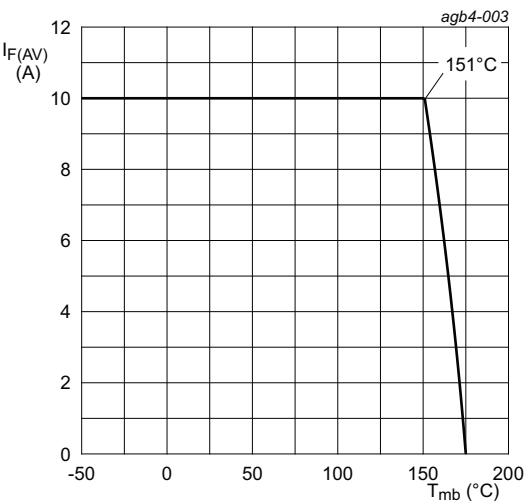


Fig. 3. Forward current as a function of mounting base temperature; maximum values; per diode

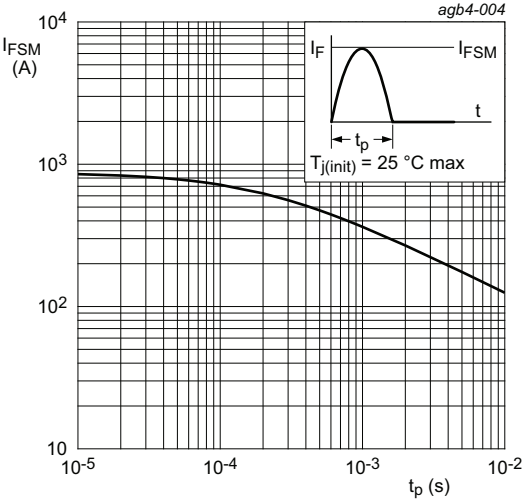


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|--|--------------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | per diode; Fig. 5 | - | - | 2.4 | K/W |
| | | both diodes conducting; Fig. 5 | - | - | 1.6 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient free air | in free air | - | 50 | - | K/W |

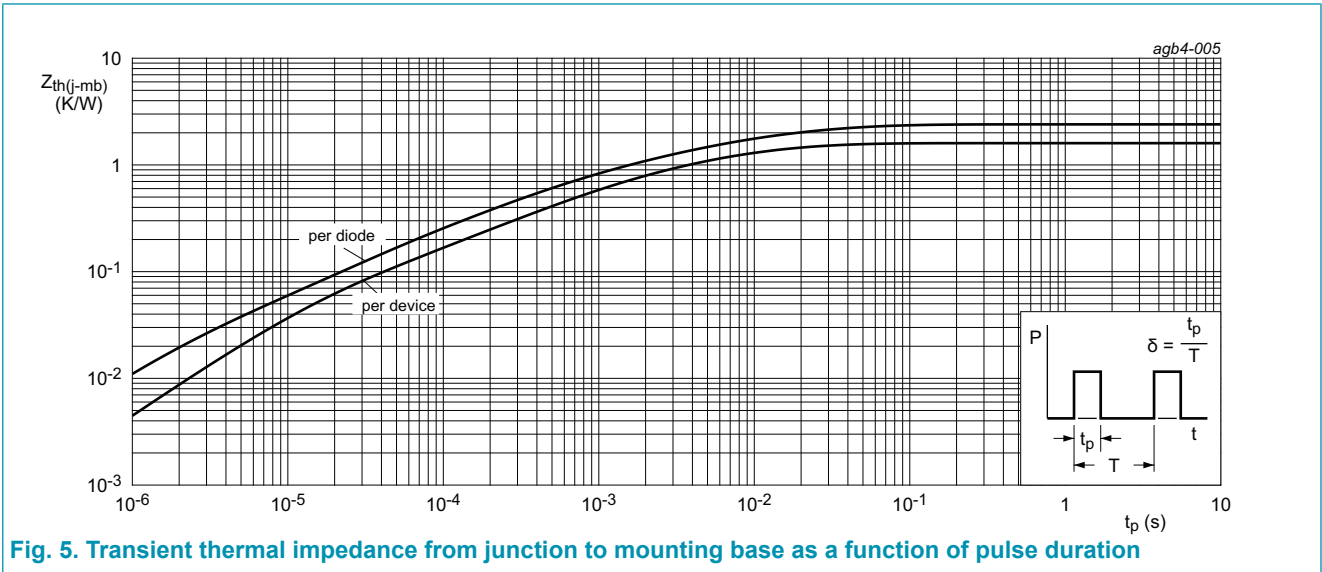
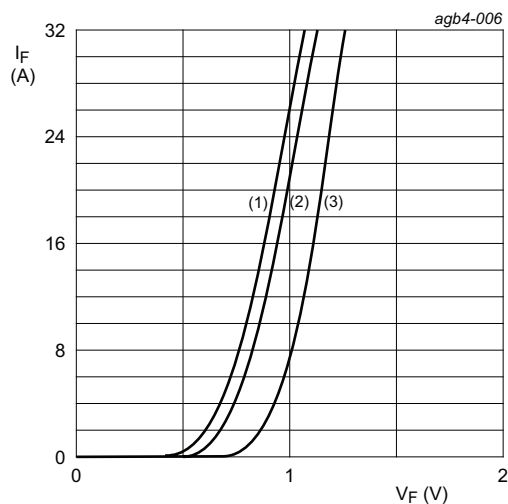


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|-------------------------|-------------------------------|--|--|-----|------|------|------|
| Static characteristics | | | | | | | |
| V _F | forward current | I _F = 20 A; T _J = 25 °C; per diode; Fig. 6 | | - | 1.06 | 1.15 | V |
| | | I _F = 10 A; T _J = 25 °C; per diode; Fig. 6 | | - | 0.95 | - | V |
| | | I _F = 8 A; T _J = 150 °C; per diode; Fig. 6 | | - | 0.76 | 0.85 | V |
| I _R | reverse current | V _R = 200 V; T _J = 25 °C; per diode | | - | 0.3 | 5 | μA |
| | | V _R = 200 V; T _J = 150 °C; per diode | | - | 70 | 250 | μA |
| Dynamic characteristics | | | | | | | |
| Q _r | reverse charge | I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _J = 25 °C; per diode; Fig. 7 | | - | 14.5 | - | nC |
| | | I _F = 2 A; V _R = 30 V; dI _F /dt = 20 A/μs; T _J = 25 °C; per diode; Fig. 7 | | | 13.5 | - | nC |
| t _{rr} | reverse recovery time | I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _J = 25 °C; per diode; Fig. 7 | | - | 18 | 25 | ns |
| I _{RM} | peak reverse recovery current | I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _J = 25 °C; per diode; Fig. 7 | | - | 1.7 | - | A |



$V_o = 0.702 \text{ V}$; $R_s = 0.0151 \text{ } \Omega$

(1) $T_j = 150 \text{ }^\circ\text{C}$; typical values

(2) $T_j = 150 \text{ }^\circ\text{C}$; maximum values

(3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode

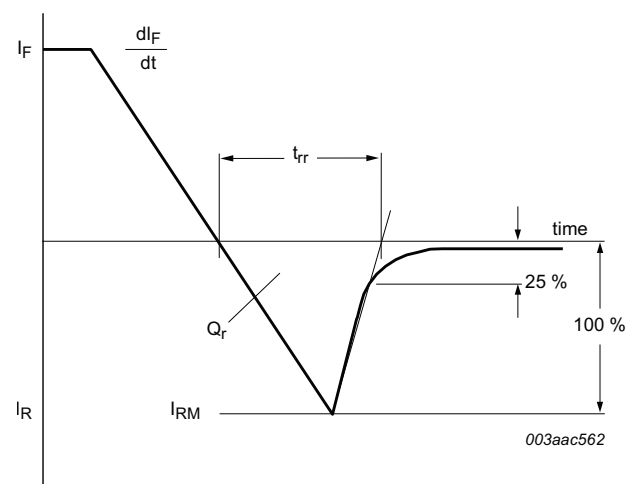
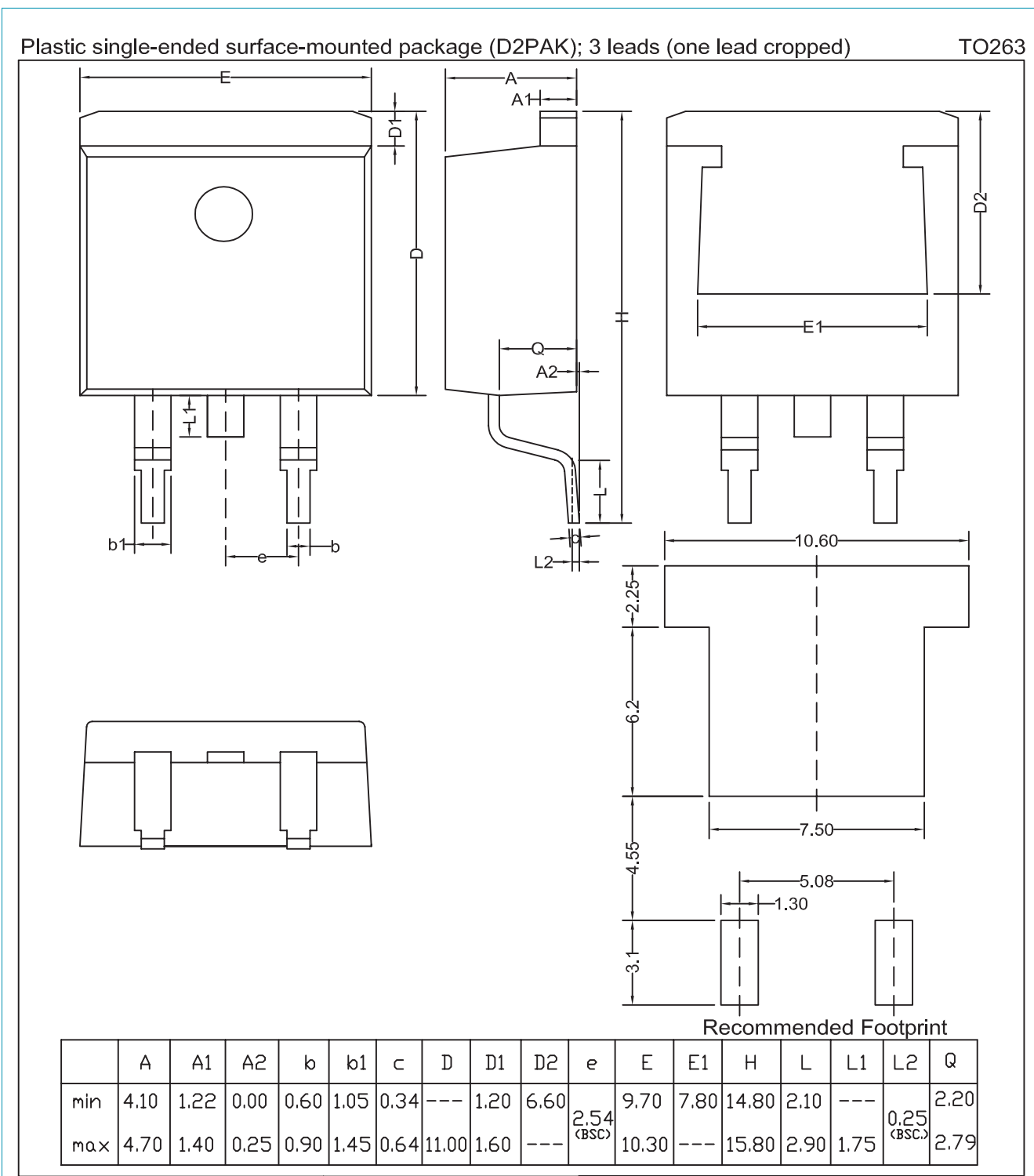


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



12. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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- [2] The term 'short data sheet' is explained in section "Definitions".
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